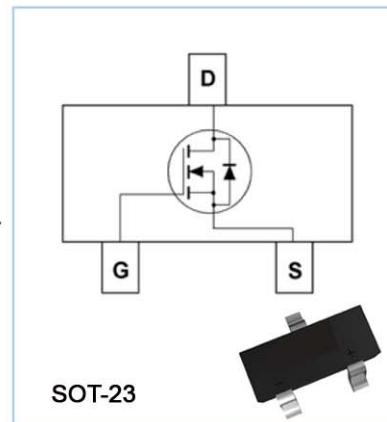


N-Channel Enhancement Mode MOSFET Feature

- 50V/0.2A, R_{DS(ON)} = 3.5 Ω (MAX) @V_{GS} = 5V. I_D = 0.2A
R_{DS(ON)} = 10 Ω (MAX) @V_{GS} = 2.75V. I_D = 0.2A
- Super High dense cell design for extremely low R_{DS(ON)}.
- Reliable and Rugged.
- Low Threshold Voltage (0.5V—1.5V) Make it Ideal for Low Voltage Applications.
- SOT-23 for Surface Mount Package.



Applications

- Power Management in DC/DC Converters、Portable and Battery-powered Products.

Absolute Maximum Ratings

T_A=25°C Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V _{DS}	50	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	0.2	A

Electrical Characteristics

T_A=25°C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	V _{GS} =0V, I _D =250μA	50	-	-	V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =50V, V _{GS} =0V	-	-	0.5	μA
		V _{DS} =25V, V _{GS} =0V	-	-	0.1	
Gate Body Leakage Current, Forward	IGSSF	V _{GS} =20V, V _{DS} =0V	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	V _{GS} =-20V, V _{DS} =0V	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D =1.0 mA	0.5	-	1.5	V
Static Drain-source On-Resistance	R _{DS(ON)}	V _{GS} = 5.0V, I _D = 0.2A	-	-	3.5	Ω
		V _{GS} = 2.75V, I _D = 0.2A	-	-	10	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0V, I _S =0.2A			2.5	V

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Typical Characteristics

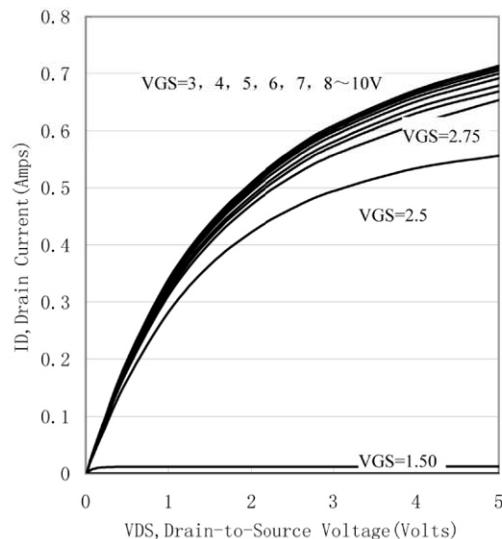


Figure 1. Output Characteristics

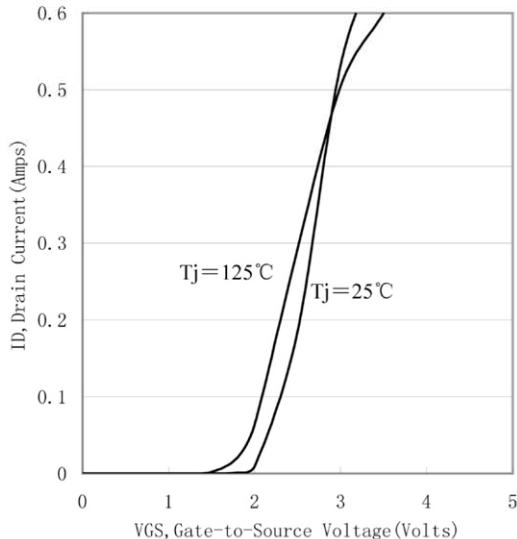


Figure 2. Transfer Characteristics

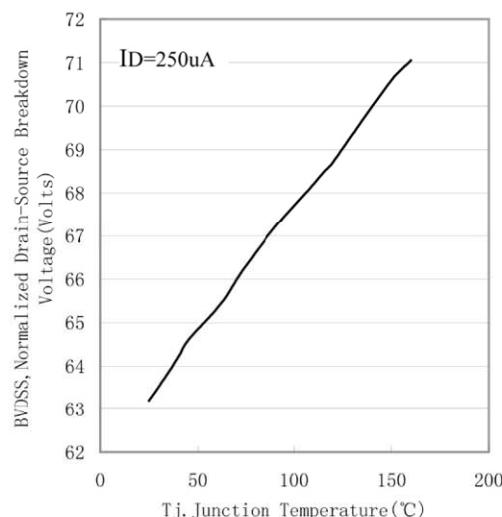


Figure 3. Breakdown Voltage Variation with Temperature

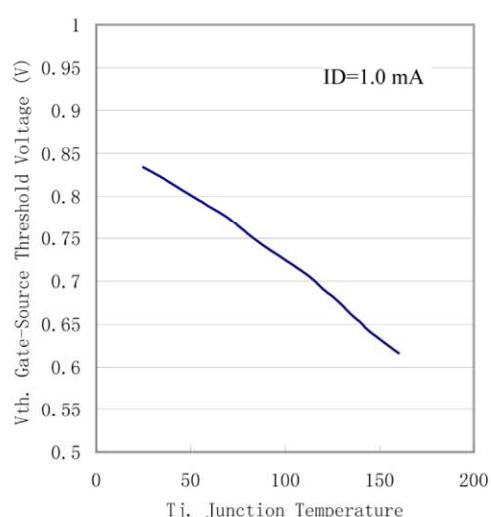


Figure 4. Gate Threshold Variation with Temperature

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Typical Characteristics

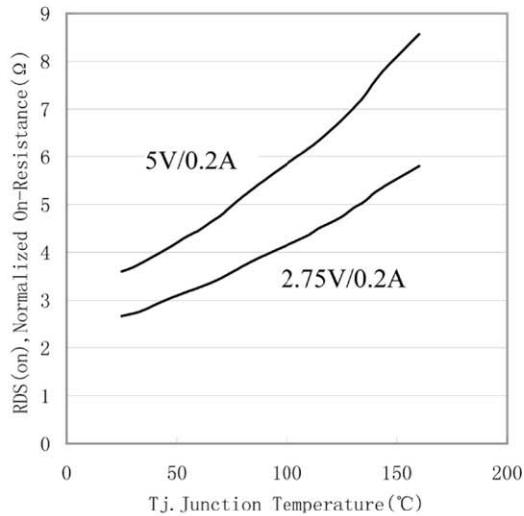


Figure 5. On-Resistance Variation with Temperature

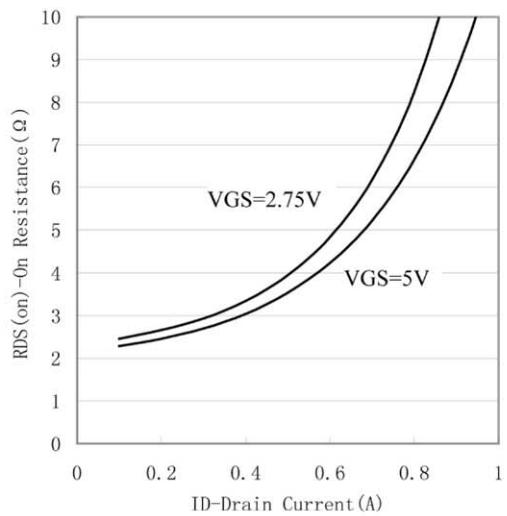


Figure 6. On-Resistance vs. Drain Current

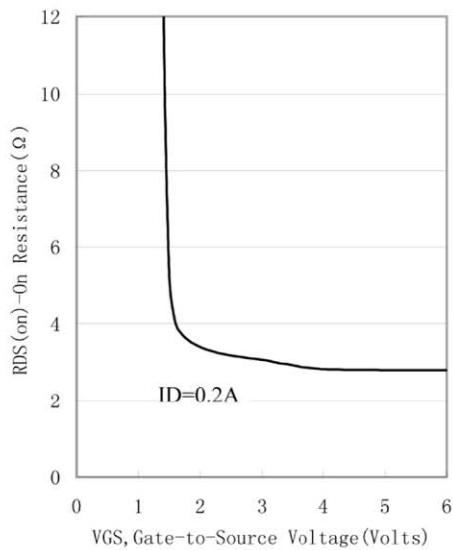


Figure 7. On-Resistance vs. Gate-to-Source Voltage

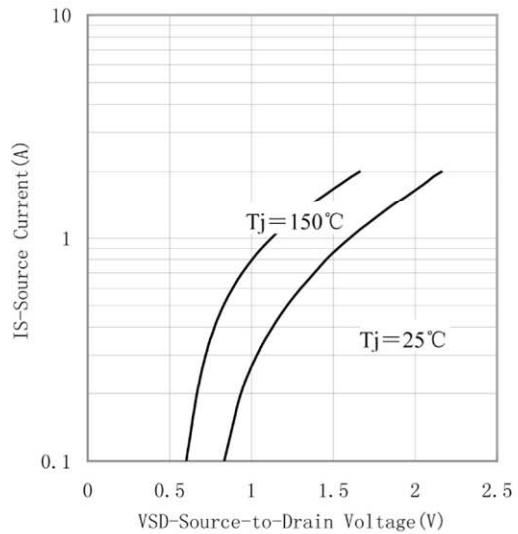


Figure 8. Source-Drain Diode Forward Voltage

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